

SOD-323 Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

■Features 特点

Low forward voltage drop 低正向压降

High current capability 高电流能力

Surface mount device 表面贴装器件

Case 封装:SOD-323



■Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherWise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	B16WS	B110WS	Unit 单位
Device Marking 产品印字		B16	B110	
Peak Reverse Voltage 反向峰值电压	V_{RRM}	60	100	V
DC Reverse Voltage 直流反向电压	V_R	60	100	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	42	70	V
ForWSard Rectified Current 正向整流电流	I_F	1		A
Peak Surge Current 峰值浪涌电流	I_{FSM}	25		A
PoWSer Dissipation 耗散功率	P_D	300		mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	400		$^{\circ}\text{C}/\text{W}$
Junction/Storage Temperature 结温/储藏温度	T_J, T_{stg}	$-65\text{to}+150^{\circ}\text{C}$		$^{\circ}\text{C}$

■Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherWise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	B16WS	B110WS	Unit 单位	Condition 条件
Reverse Voltage 反向电压	V_R	60	100	V	$I_R=1\text{mA}$
ForWSard Voltage 正向电压	V_F	0.7	0.85	V	$I_F=1\text{A}$
Reverse Current 反向电流	I_R	0.02($T_A=25^{\circ}\text{C}$) 5($T_A=100^{\circ}\text{C}$)		mA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_T	30		pF	$V_R=4\text{V}, f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

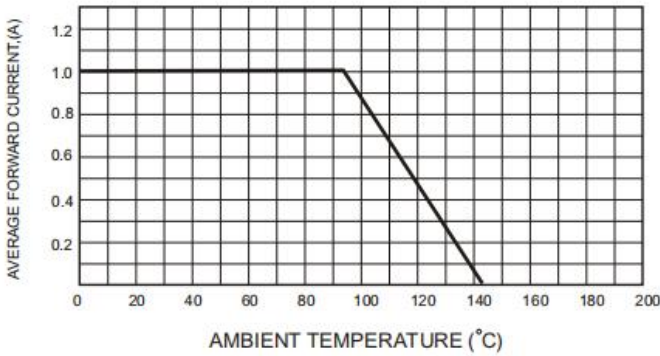


FIG.3 - Power Derating Curve

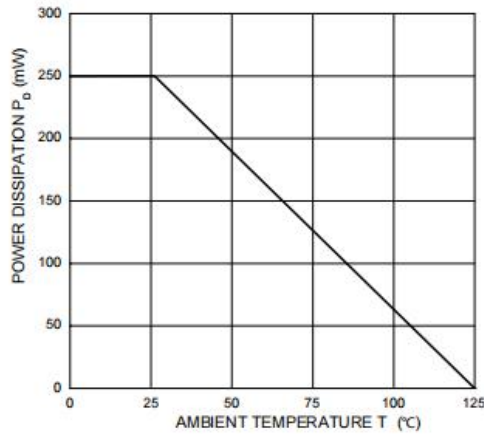


FIG.4-TYPICAL JUNCTION CAPACITANCE

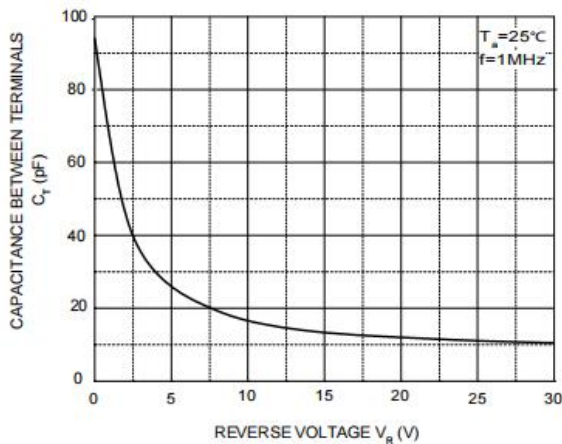


FIG.2-TYPICAL FORWARD CHARACTERISTICS

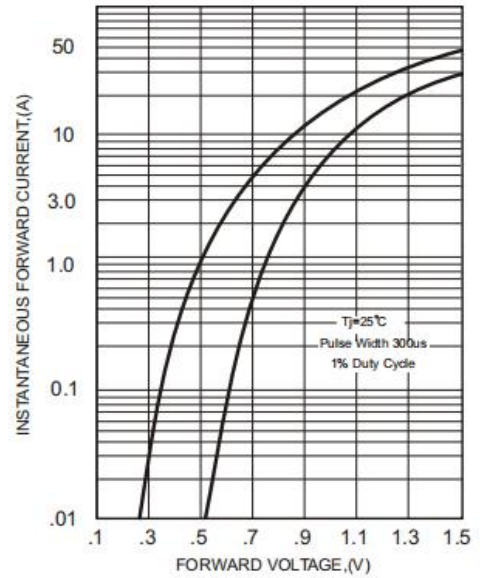
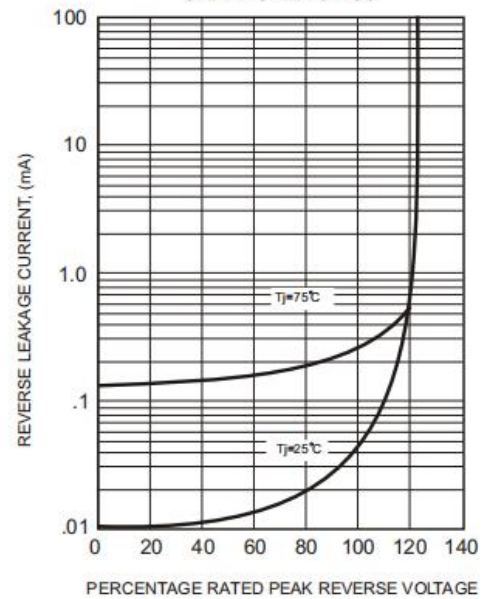
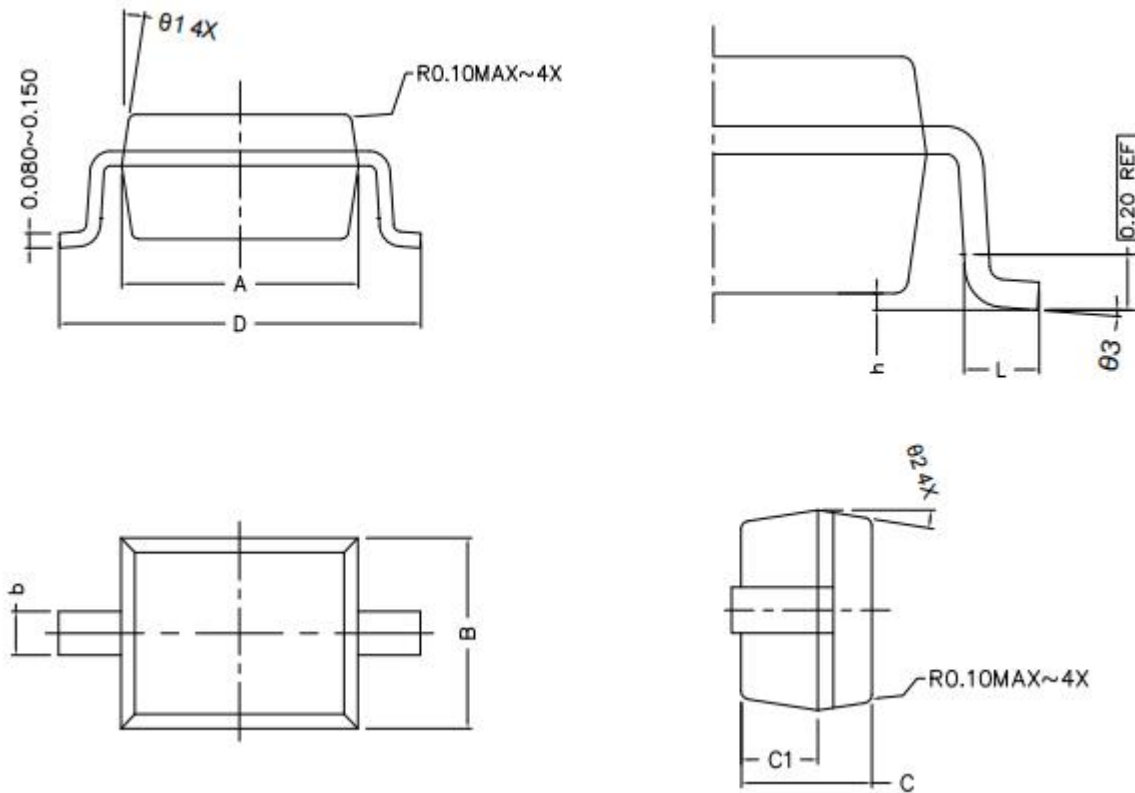


FIG.5 - TYPICAL REVERSE CHARACTERISTICS



■ **Dimension 外形封装尺寸**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.600	1.800	0.063	0.071
B	1.200	1.400	0.047	0.055
C	0.750	0.950	0.030	0.037
C1	0.450	0.550	0.018	0.022
D	2.450	2.800	0.096	0.110
L	0.200	0.400	0.008	0.016
b	0.200	0.400	0.008	0.016
h	0.020	0.120	0.001	0.005
$\ominus 3$	0°	8°	0°	8°